Attorney Reference No.: SAM-0508

Declaration, Petition and Power of Attorney for Patent Application

As a below named inventor, I hereby declare that:

My residence, mailing address, and citizenship are as stated below next to my name,

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled:

METHOD OF FORMING GATE OXIDE LAYER IN SEMICONDUCTOR DEVICE

the speci	fication	of which (check only one):
	X	is attached hereto; or
	_	was filed as United States or PCT International Application Serial No on, and was amended on (if applicable).
I hereby by any a	state the	at I have reviewed and understand the contents of the specification, including the claims as amended ant referred to herein.
with Titl available	le 37 C.I e betwee	ne duty to disclose information which is material to the examination of this application in accordance F.R. §1.56, including for continuation-in-part applications, material information which became n the filing date of the prior application and the national or PCT international filing date of the part application.
for pater other the patent or United S	nt or inv in the U r invente States of	preign priority benefits under 3S U.S.C. §119(a)-(d) or (f), or §365(b) of any foreign application(s) entor's certificate or §365(a) of any PCT international application(s) designating at least one country nited States of America listed below and ha ve also identified below any foreign application(s) for or's certificate or any PCT international application(s) designating at least one country other than the America filed by me on the same subject matter having a filing date before that of the application(s) is claimed.
	Pr	ior foreign/PCT application(s) and priority claims under 35 U.S.C. §119(a)-(d) or §365

Country	Application Number	Filing Date (day, month, year)
Korea	02-76230	3 December 2002

I hereby claim the benefit under 35 U.S.C. §119(e) of any United States provisional application(s) listed below.

Prior U.S. applications for benefit under 35 U.S.C. §119(e)

Application Number	Filing Date	
	· · · · · · · · · · · · · · · · · · ·	

I hereby claim the benefit under 35 U.S.C.§ 120 of any United States application(s) or PCT international

Attorney Reference No.: SAM-0508

application(s) designating the United States of America that is/are listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in that/those prior application(s) in the manner provided by the first paragraph of 35 U.S.C. § 112, 1 ac knowledge the duty to disclose material information as defined in 37 C.F.R. § 1.56 which occurred between the filing date of the prior a pplications and the national or PCT international filing date of this application:

Prior U.S. Applications or PCT International Applications designating the U.S. for benefit under 35 U.S.C. § 120

Application Number	Filing Date (day, mouth, year)	Status (issued, pending, abandoned)

As a named inventor, I hereby appoint the following attorn eys and/or agents to prosecute this application and transact all business in the Patent and Trademark Office connected therewith:

Steven M. Mills Reg. No. 36,610 David Silverstein Reg No. 26,336 Anthony P. Onello, Jr. Reg. No.

Reg. No. 38,572

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Wherefore I petition that letters patent be granted to me for the invention or discovery described and claimed in the attached specification and claims, and hereby subscribe my name to said specification and claims and to the foregoing declaration, power of attorney, and this petition.

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under 18 U.S.C. 1001 and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

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